

# MOSFET – N-Channel, POWERTRENCH®

**80 V, 100 A, 4.2 mΩ**

## FDD86367

### Features

- Typical  $R_{DS(on)} = 3.3 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- Typical  $Q_{g(\text{tot})} = 68 \text{ nC}$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- UIS Capability
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

### Applications

- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12 V Systems

### MOSFET MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-to-Source Voltage	80	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $V_{GS} = 10$ ) $T_C = 25^\circ\text{C}$	100	A
	Pulsed Drain Current $T_C = 25^\circ\text{C}$	See Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	82	mJ
$P_D$	Power Dissipation	227	W
	Derate Above $25^\circ\text{C}$	1.52	W/ $^\circ\text{C}$
$T_J$ , $T_{STG}$	Operating and Storage Temperature	-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.66	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	52	$^\circ\text{C}/\text{W}$

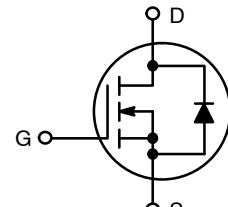
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 40 \mu\text{H}$ ,  $I_{AS} = 64 \text{ A}$ ,  $V_{DD} = 80 \text{ V}$  during inductor charging and  $V_{DD} = 0\text{V}$  during time in avalanche.
3.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

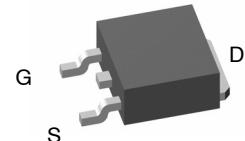


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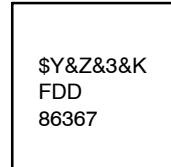


N-Channel



DPAK3 (TO-252 3 LD)  
CASE 369AS

### MARKING DIAGRAM



FDD86367 = Specific Device Code  
\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = 3-Digit Date Code  
&K = 2-Digits Lot Run Traceability Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FDD86367

## PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping <sup>†</sup>
FDD86367	FDD86367	DPAK3 (TO-252 3 LD) (Pb-Free)	13"	16 mm	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

B <sub>VDSS</sub>	Drain-to-Source Breakdown Voltage	I <sub>D</sub> = 250 $\mu$ A, V <sub>GS</sub> = 0 V	80	—	—	V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	T <sub>J</sub> = 25°C	—	—	1 mA
			T <sub>J</sub> = 175°C (Note 4)	—	—	1 mA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>GS</sub> = $\pm$ 20 V		—	—	$\pm$ 100 nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 $\mu$ A	2	3	4	V
R <sub>DS(on)</sub>	Drain to Source On Resistance	I <sub>D</sub> = 80 A, V <sub>GS</sub> = 10 V	T <sub>J</sub> = 25°C	—	3.3	4.2 m $\Omega$
			T <sub>J</sub> = 175°C (Note 4)	—	6.6	8.4 m $\Omega$

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	4840	—	pF	
C <sub>oss</sub>	Output Capacitance		—	814	—	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance		—	31	—	pF	
R <sub>g</sub>	Gate Resistance	V <sub>GS</sub> = 0.5 V, f = 1 MHz		—	2.3	$\Omega$	
Q <sub>g(TOT)</sub>	Total Gate Charge	V <sub>GS</sub> = 0 to 10 V	V <sub>DD</sub> = 40 V, I <sub>D</sub> = 80 A	—	68	88 nC	
Q <sub>g(th)</sub>	Threshold Gate Charge	V <sub>GS</sub> = 0 to 2 V		—	8.8	— nC	
Q <sub>gs</sub>	Gate-to-Source Gate Charge	V <sub>DD</sub> = 40 V, I <sub>D</sub> = 80 A		—	22	— nC	
Q <sub>gd</sub>	Gate-to-Drain "Miller" Charge			—	14	— nC	

### SWITCHING CHARACTERISTICS

t <sub>on</sub>	Turn-On Time	V <sub>DD</sub> = 40 V, I <sub>D</sub> = 80 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 $\Omega$	—	—	104	ns
t <sub>d(on)</sub>	Turn-On Delay		—	20	—	ns
t <sub>r</sub>	Rise Time		—	49	—	ns
t <sub>d(off)</sub>	Turn-Off Delay		—	36	—	ns
t <sub>f</sub>	Fall Time		—	16	—	ns
t <sub>off</sub>	Turn-Off Time		—	—	80	ns

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source-to-Drain Diode Voltage	I <sub>SD</sub> = 80 A, V <sub>GS</sub> = 0 V	—	—	1.3	V
		I <sub>SD</sub> = 40 A, V <sub>GS</sub> = 0 V	—	—	1.2	V
t <sub>rr</sub>	Reverse-Recovery Time	V <sub>DD</sub> = 64 V, I <sub>F</sub> = 80 A, dI <sub>SD</sub> /dt = 100 A/ $\mu$ s	—	68	102	ns
			—	66	106	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at T<sub>J</sub> = 175°C. Product is not tested to this condition in production.

## TYPICAL CHARACTERISTICS

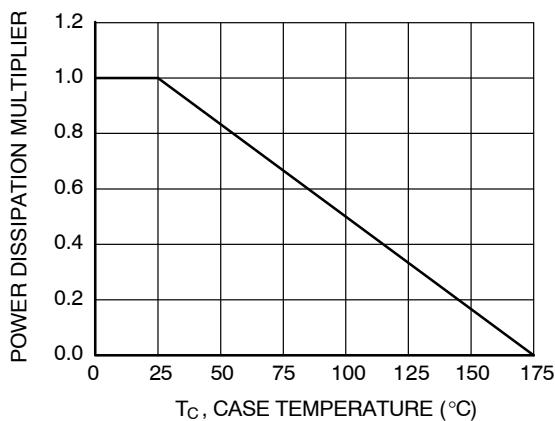


Figure 1. Normalized Power Dissipation vs. Case Temperature

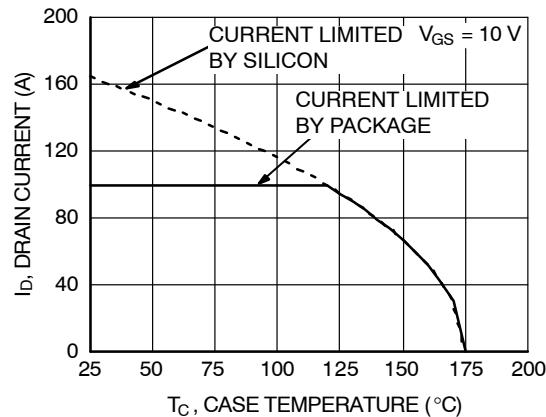


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

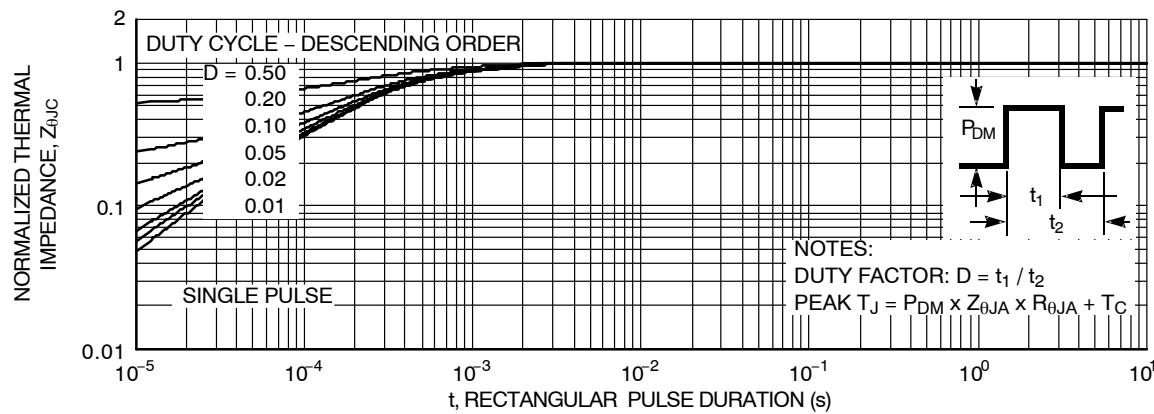


Figure 3. Normalized Maximum Transient Thermal Impedance

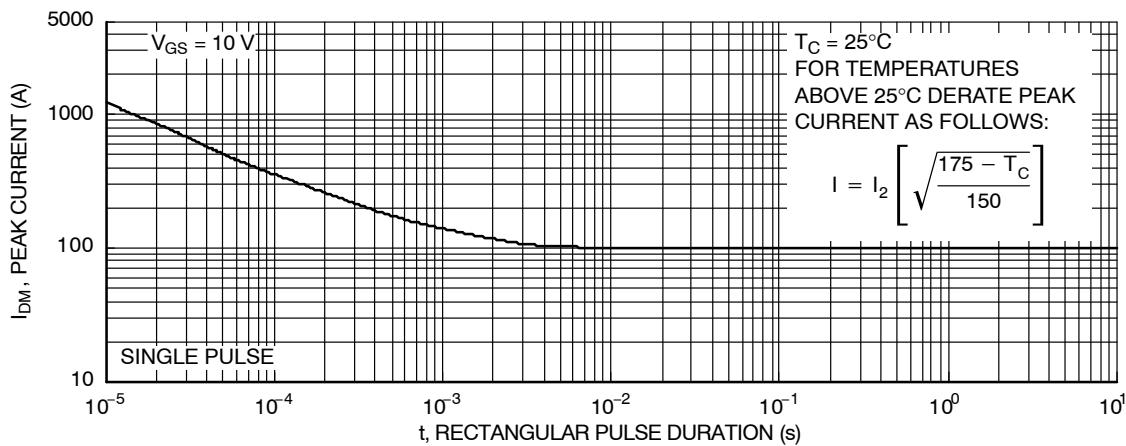


Figure 4. Peak Current Capability

## TYPICAL CHARACTERISTICS (continued)

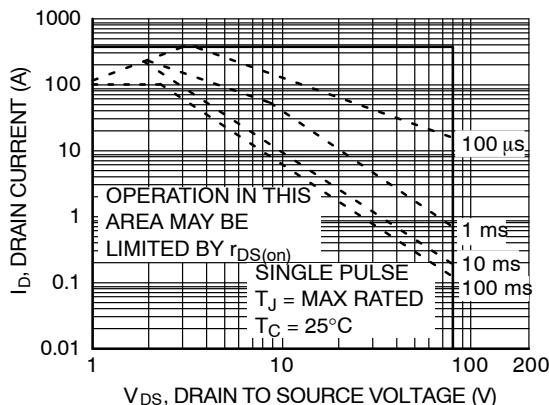


Figure 5. Forward Bias Safe Operating Area

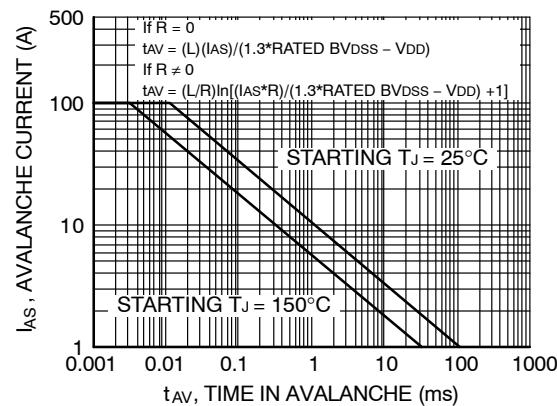
NOTE: Refer to ON Application Notes [AN7514](#) and [AN7515](#)

Figure 6. Unclamped Inductive Switching Capability

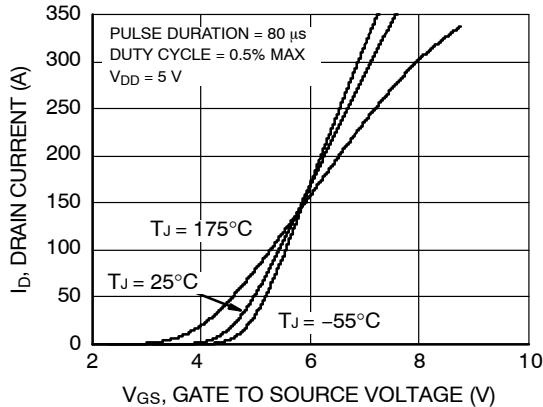


Figure 7. Transfer Characteristics

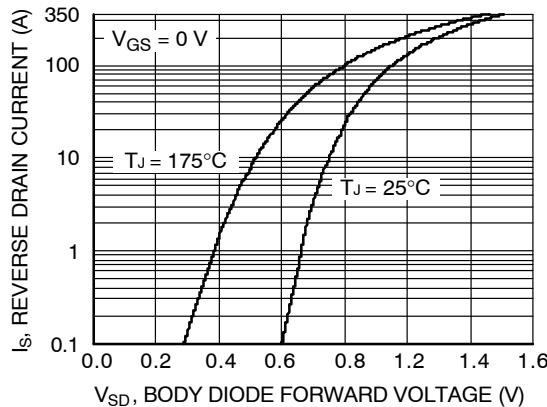


Figure 8. Forward Diode Characteristics

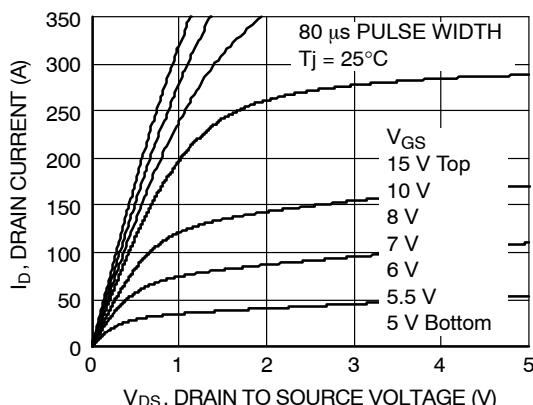


Figure 9. Saturation Characteristics

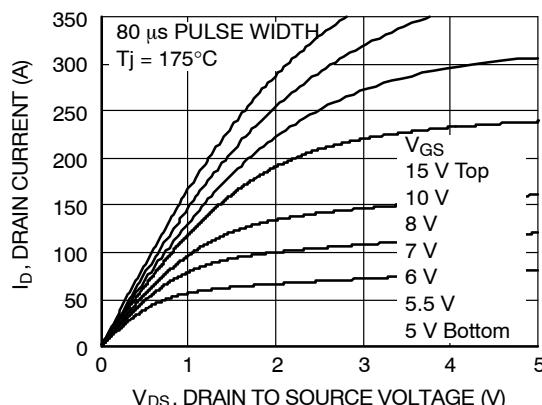


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

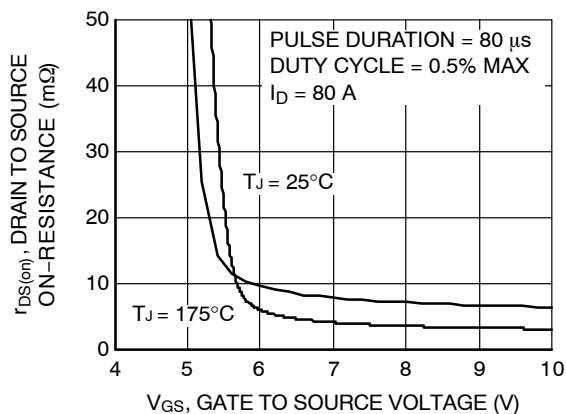


Figure 11.  $R_{DS(on)}$  vs. Gate Voltage

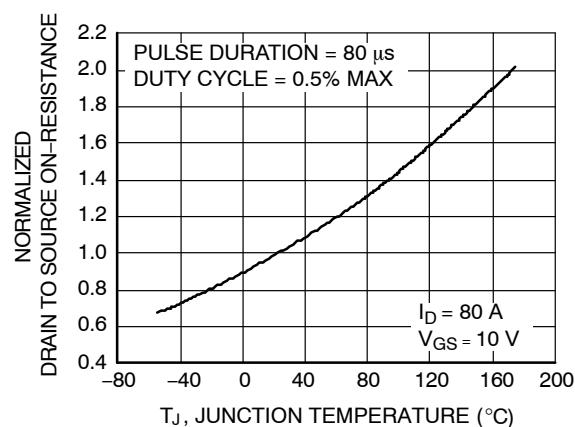


Figure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

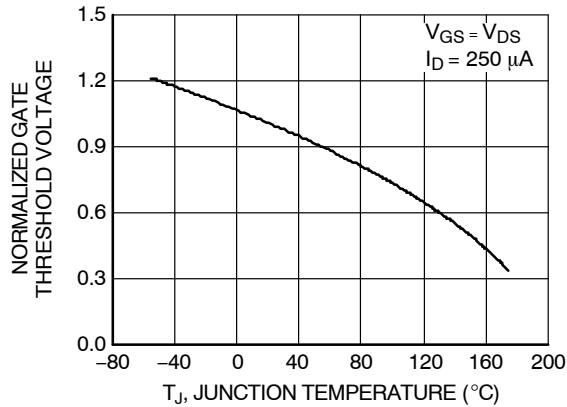


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

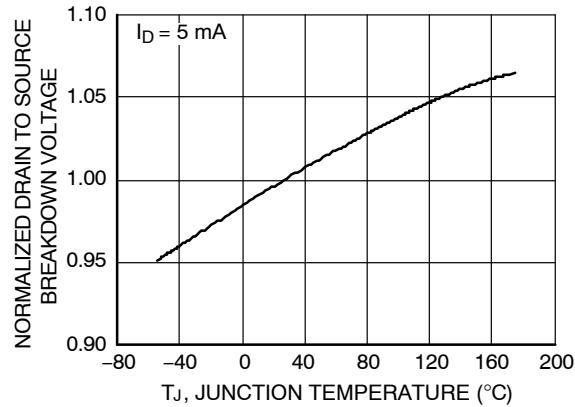


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

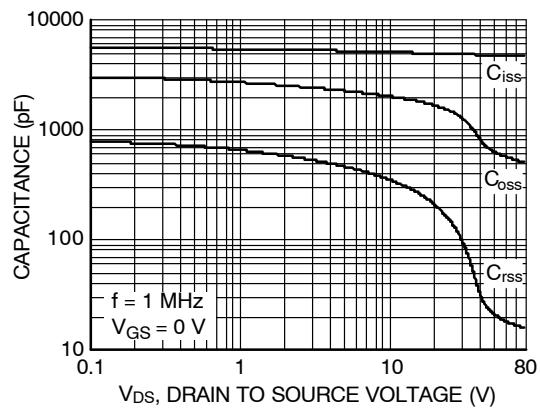


Figure 15. Capacitance vs. Drain to Source Voltage

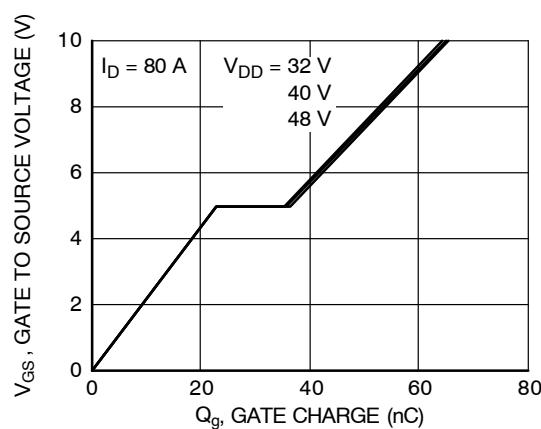
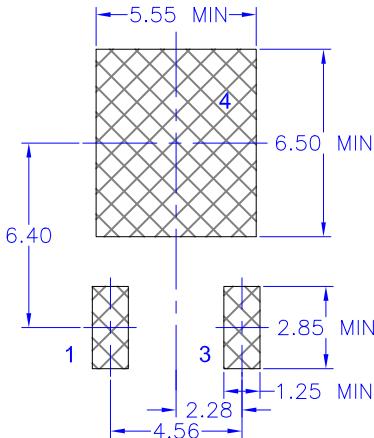
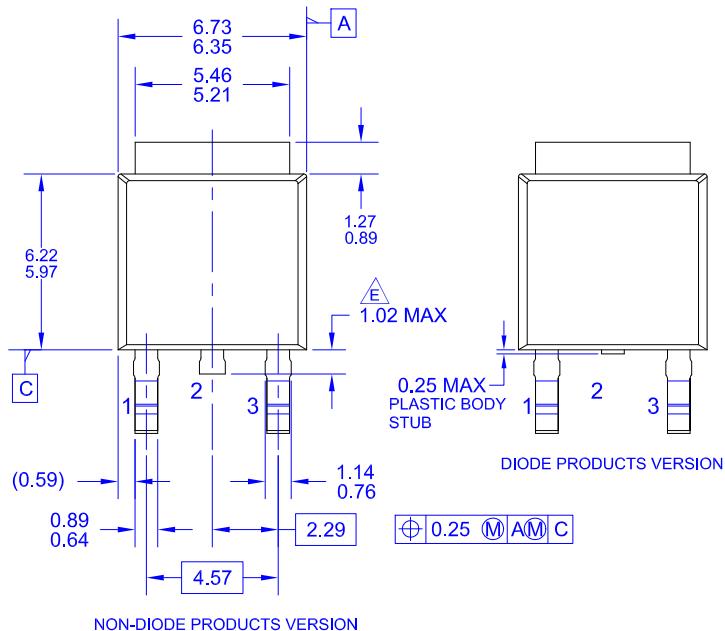


Figure 16. Gate Charge vs. Gate to Source Voltage

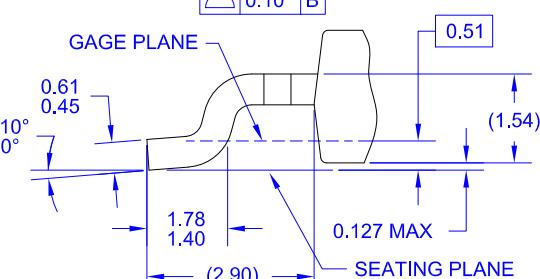
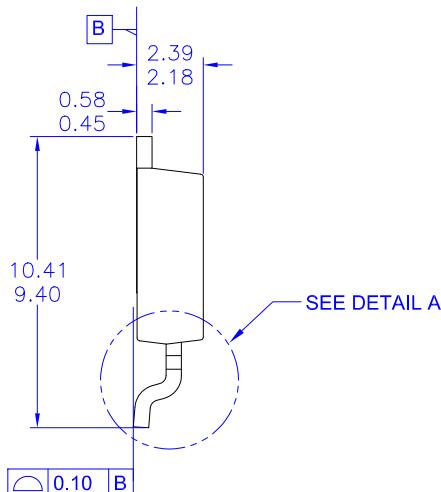
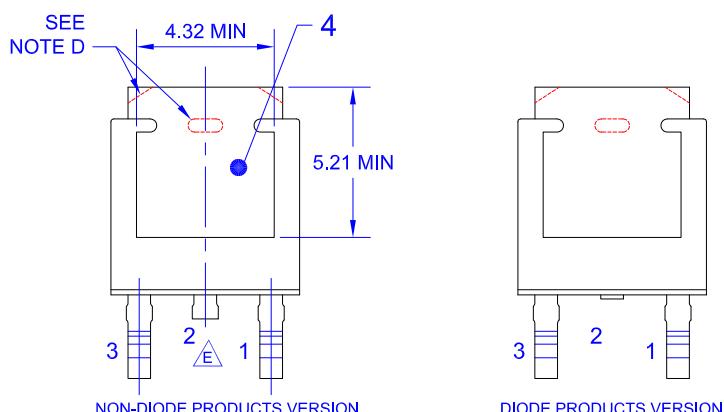
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**DPAK3 (TO-252 3 LD)**  
CASE 369AS  
ISSUE O

DATE 30 SEP 2016



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